BC 556 through

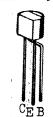
BC 560

PNP SILICON AF SMALL SIGNAL TRANSISTORS

THE BC556 THROUGH BC560 ARE PNP SILICON PLANAR EPITAXIAL TRANSISTORS FOR USE IN AF SMALL SIGNAL AMPLIFIER STAGES AND DIRECT COUPLED CIRCUITS. THEY ARE COMPLEMENTARY TO BC546 THROUGH BC550.

THE BC559, BC560 ARE CHARACTERIZED BY LOW NOISE FIGURE.

CASE TO-92F



ABSOLUTE MAXIMUM RATINGS		BC556	BC557	BC558	BC559	BC560
Collector-Base Voltage	-ACBO	807	50 v	30 V	30 V	50 v
Collector-Emitter Voltage ($V_{ m BE}=0$)	-Vces	VO 8	50 v	30 v	30 v	50 v
Collector-Emitter Voltage (IB=0)	-ACEO	65 ₹	45 ₹	30V	30V	45 ₹
Emitter-Base Voltage	$-v_{\mathrm{EBO}}$			5 v		
Collector Current	-IC			LOOmA		
Collector Peak Current	-ICM			200mA	•	
Collector-Emitter Voltage (IB=0) -VCEO Emitter-Base Voltage -VEBO Collector Current -IC		đ	erate 4	500mW mW/ cc a	.bo ve 25	,oc

Operating Junction & Storage Temperature Tj, Tstg

-55 to 150°C

ELECTRICAL CHARACTERISTICS (TA= 25° C unless otherwise noted)

ELECTRICAL CHARACTERISTICS (A=25°C	unless	Omer	MTDE	no ced /		
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	-BVCBO	-				IC=10µA IE=0
BC556	- 1020	80			V	ş» - /
BC557		50			A	····
BC558		30 30 50			V	
BC 559		30			∀	
BC 560		50			▼	
Collector-Emitter Breakdown Voltage	-BVCES					-Ic=10µA VBE=0
BC556		80			\ \ \ \ \ \	,
BC557		50			₩	:
BC558		30			\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \	
BC559		30			V	
вс560		50			V	
Collector-Emitter Breakdown Voltage	-LVCEO					-Ic=2mA(Pulsed)
BC556		65			₩ ₩	IB=0
BC557		45			V	
BC558		30			V	, s
BC559		30			V	
вс560		45		<u>,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,</u>	V	

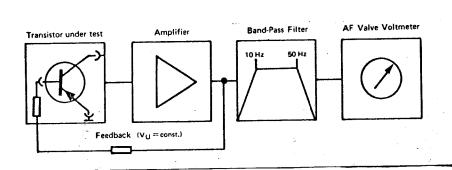
MICRO ELECTRONICS LTD.

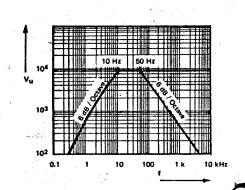
38 HUNG TO ROAD, KWUN TONG, HONG KONG. KWUN TONG P. O. BOX69477 CABLE ADDRESS 'TELEPHONE:- 3-430181-6 3-893363.

FAX: 3-410321

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST, CONDITIONS		
Emitter-Base Breakdown Voltage	-BV _{EBO}	5			Λ	-IE=Jhy IC=0		
Collector Cutoff Current	-ICBO			15	nA	-V _{CB} =30V I _E =0		
				5	μΑ	-VCB=30V IE=0 TA=150°C		
Collector-Emitter Saturation Voltage	-VCE(sat)		0.1	-	v	-IC=10mA -IB=0.5mA		
			0.25	0.65	V	-IC=100mA -IB=5mA(Pulsed)		
Collector-Emitter Knee Voltage	-VCEK		0.3	0.6	٧	-Ic=10mA, IB=value at which -IC=11mA -VCE=1V		
Base-Emitter Saturation Voltage	-VBE(sat)		0.72		V	-IC=10mA -IB=0.5mA		
			0.92		v	-IC=100mA -IB=5mA(Pulsed)		
Base-Emitter Voltage	-VBE	0.6	0.65	0.75	v	-IC=2mA -VCE=5V		
-			0.7	0.82	V	-IC=10mA -VCE=5V		
Current Gain-Bandwidth Product	fŢ		,180		MHz	-IC=10mA -VCE=5V		
Collector-Base Capacitance	Cob		3.2	, <u> </u>	pF	-VCB=10V IE=0 f=1MHz		
Noise Figure	NF					-IC=0.2mA -VCE=5V		
BC556,557,558			2	10	dB	$RG=2K\alpha$ $f=1kHz$		
BC559,560			1.2	4	dB	△f=200Hz		
Noise Figure	NF		· · · · · ·			-IC=0.2mA -VCE=5V		
BC559 only			1.2	4	dB	RG=2KA f=30Hz-15KHz		
BC560 only			1.2	2	dB			
Flicker Noise Voltage Referred to	<u>En</u>					-IC=0.2mA -VCE=5V		
Base BC559,560 only				0.11	μV	R _G =2Ka f=10-50Hz		

FLICKER NOISE MEASUREMENT





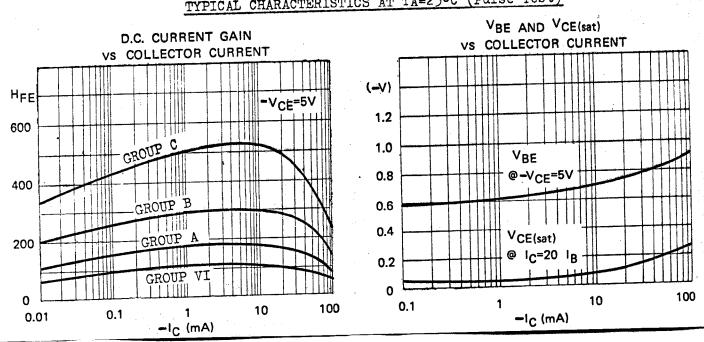
D.C. CURRENT GAIN (HFE) AT -VCE=5V TA=25°C

		BC556, BC557 BC558			BC556, BC557 BC558		BC556, BC557 BC558			BC558			
7	@ -IC	HFE	GROUP		HF	BC559, BC560 HFE GROUP A		BC559, BC560 HFE GROUP B			BC559, BC560 HFE GROUP C MIN TYP MAX		
		MIN	TYP	MIN	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TIP	MAA
	O.OlmA		70			110			200			330	
	2mA	70	110	140	110	170	220	200	300	450	420	520	800
	100mA		60			80			140			240	

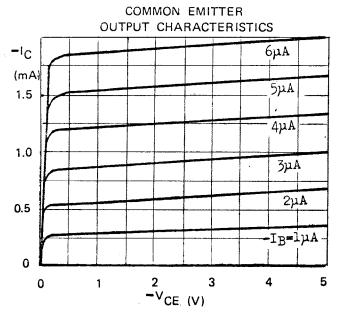
-IC=2mA -VCE=5V f=1KHz TA=25°C

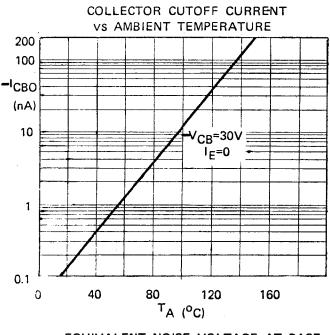
n - PARAMETERS AT	IIA OII					
h - PARAMETER	SYMBOL	HFE GROUP VI	HFE GROUP A	HFE GROUP B	HFE GROUP C	UNE
	BILIBOR	MIN TYP MAX	MIN TYP MAX	MIN TYP MAX	MIN TYP MAX	
Input Impedance	hie	1.4	2.7	4•5	8.7	Κn
Voltage Feedback Ratio	hre	2.5	~ 3	3. 5	4	x1 0 ⁴
Small Signal Current Gain	hfe	75 110 150	125 190 260	240 330 500	450 580 900	
Output Admittance	hoe	20	25	3 5	60	μσ

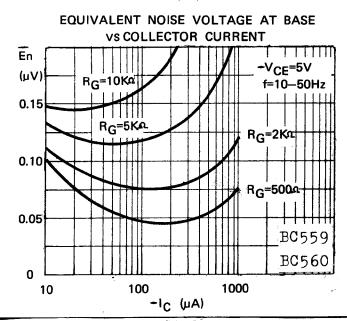
TYPICAL CHARACTERISTICS AT TA=250C (Pulse Test)

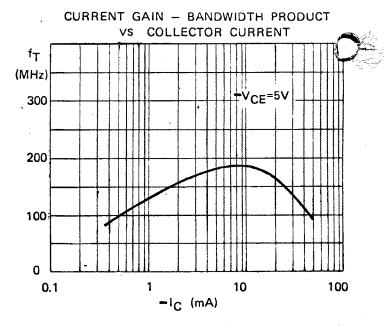


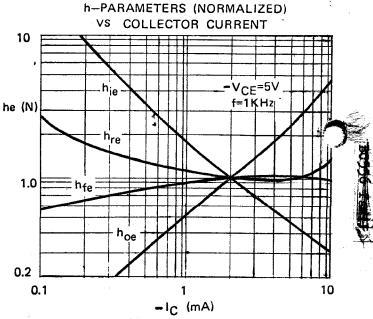
TYPICAL CHARACTERISTICS (TA=25°C UNLESS OTHERWISE SPECIFIED)

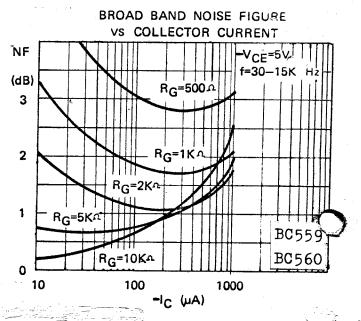












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